

PNP Germanium Transistors

**AC 121
AC 152**

SIEMENS AKTIENGESELLSCHAFT

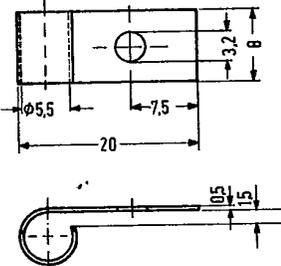
for AF, driver and output stages of medium performance

AC 121 and AC 152 are alloyed germanium PNP transistors in 1 A 3 DIN 41871 metal case (similar to TO 1).

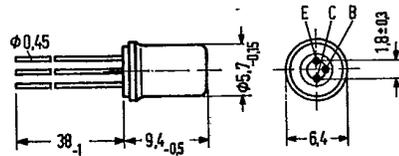
The leads of these transistors are electrically insulated from the case. The collector terminal is marked by a red dot at the rim of the case. For use in push-pull output stages, the transistors AC 121 and AC 152 are available in pairs. A fixing part (heat sink¹⁾) is provided for fixing on the chassis; it has to be ordered separately.

Not for new design

| Type | Ordering code | Type | Ordering code |
|---------------|----------------|---------------|---------------|
| AC 121 IV | Q60103-D121 | AC 152 IV | Q60103-X152-D |
| AC 121 V | Q60103-E121 | AC 152 V | Q60103-X152-E |
| AC 121 VI | Q60103-F121 | AC 152 VI | Q60103-X152-F |
| AC 121 VII | Q60103-G121 | AC 152 paired | Q60103-X152-P |
| AC 121 paired | Q60103-P121-X1 | Heat sink | Q62901-B1 |



Approx. weight 2 g



Approx. weight 1 g

Dimensions in mm

Maximum ratings

| | AC 121 | AC 152 | | |
|---|-------------------|------------|-----|----|
| Collector-emitter voltage | -V _{CEO} | 20 | 24 | V |
| Collector-emitter voltage (V _{BE} ≥ 0.2 V) | -V _{CEV} | 20 | 32 | V |
| Collector-base voltage | -V _{CBO} | 20 | 32 | V |
| Emitter-base voltage | -V _{EBO} | 10 | 10 | V |
| Collector current | -I _C | 300 | 500 | mA |
| Base current | -I _B | 60 | 100 | mA |
| Junction temperature | T _J | 90 | 90 | °C |
| Storage temperature range | T _{stg} | -55 to +75 | | °C |
| Total power dissipation | P _{tot} | 900 | 900 | mW |

Thermal resistance

| | R _{thJA} | R _{thJC} | |
|-------------------------|-------------------|-------------------|-----|
| Junction to ambient air | ≤300 | ≤300 | K/W |
| Junction to case | ≤50 | ≤50 | K/W |

¹⁾ Thermal resistance between transistor case and heat sink below the fixing screw at careful mounting: R_{th} ≤ 10 K/W

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

The transistors AC 121, AC 152 are grouped according to the DC current gain h_{FE} at $-I_C = 100\text{ mA}$, and marked by the Roman numerals. The following values apply at a collector voltage of $-V_{CE} = 0.5\text{ V}$ and the following collector currents:

| h_{FE} group | | IV | V | VI | VII | |
|----------------|--------------|-----------------------|-----------------------|-----------------------|-----------------------|------------------------------|
| | | AC 152 | AC 152 | AC 152 | - | AC 152 |
| Type | | AC 121 |
| $-I_C$ mA | $-I_C$ mA | h_{FE} I_C/I_B | h_{FE} I_C/I_B | h_{FE} I_C/I_B | h_{FE} I_C/I_B | $-V_{BE}$ V |
| [2] | 3 | 48 [47] | 80 [78] | 115 [114] | 200 | 0.13 (<0.22) |
| 100 | 100 | 45 (30 to 60) | 75 (50 to 100) | 110 (75 to 150) | 190 (125 to 250) | 0.32 (<0.55) |
| [500] | 300 | 35 [28] | 58 [47] | 86 [68] | 148 | 0.44 (<0.8) [0.52 (<1.0)] |

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Collector-emitter saturation voltage
 ($-I_C = 100\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 ($-I_C = 300\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 Emitter cutoff current ($-V_{EBO} = 10\text{ V}$)
 Collector cutoff current ($-V_{CBO} = 20\text{ V}$)
 Collector cutoff current
 ($-V_{CEV} = 20\text{ V}$; $V_{BE} \geq 0.2\text{ V}$)

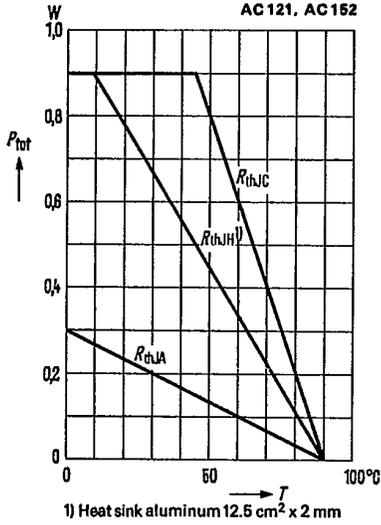
| | AC 121 | |
|-------------------|----------------------------|---------------|
| $-V_{CEsat}^{1)}$ | 0.11 (<0.3) | V |
| $-V_{CEsat}^{1)}$ | 0.15 (<0.35) | V |
| $-V_{CEsat}$ | 0.28 (<0.45) ²⁾ | V |
| $-I_{EBO}$ | 4 (<25) | μA |
| $-I_{CBO}$ | 5 (<25) | μA |
| $-I_{CEV}$ | 5 (<25) | μA |

Collector-emitter saturation voltage
 ($-I_C = 100\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 ($-I_C = 300\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 Collector cutoff current ($-V_{CBO} = 32\text{ V}$)
 Collector cutoff current ($-V_{CEV} = 32\text{ V}$;
 $V_{BE} = 0.2\text{ V}$)
 Emitter cutoff current ($V_{EBO} = 10\text{ V}$)

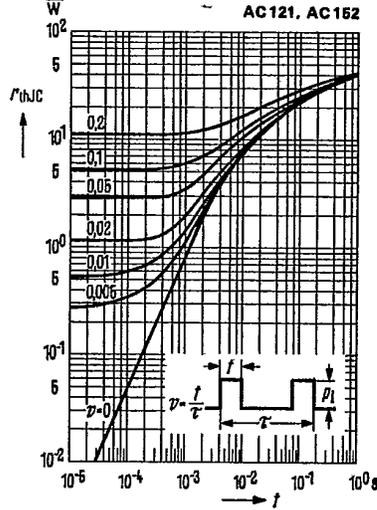
| | AC 152 | |
|-------------------|---------------------------|---------------|
| $-V_{CEsat}^{1)}$ | 0.11 (<0.18) | V |
| $-V_{CEsat}^{1)}$ | 0.15 (<0.25) | V |
| $-V_{CEsat}$ | 0.32 (<0.5) ²⁾ | V |
| $-I_{CBO}$ | 6 (<25) | μA |
| $-I_{CEV}$ | 6 (<25) | μA |
| $-I_{EBO}$ | 4 (<25) | μA |

1) The transistor is overloaded to such a degree that the DC current gain decreases to $h_{FE} = 20$.
 2) ($-I_C = 500\text{ mA}$ for the characteristic which, at a constant base current, intersects the operating point, where $-I_C = 550\text{ mA}$; $-V_{CE} = 0.5\text{ V}$)

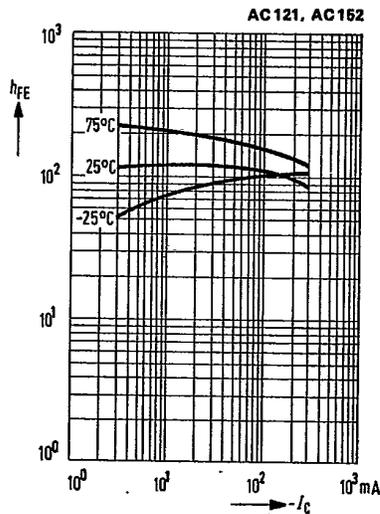
Total perm. power dissipation versus temperature
 $P_{tot} = f(T); R_{th} = \text{parameter}$



Permissible pulse load
 $r_{thJC} = f(t); v = \text{parameter}$

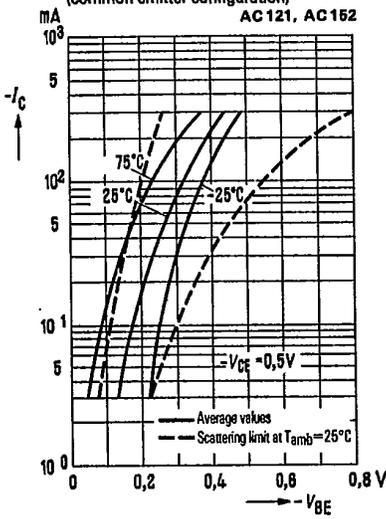


DC current gain $h_{FE} = f(I_C)$
- $V_{CE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$
(common emitter configuration)

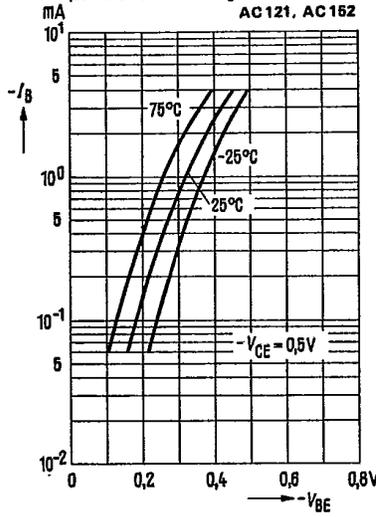


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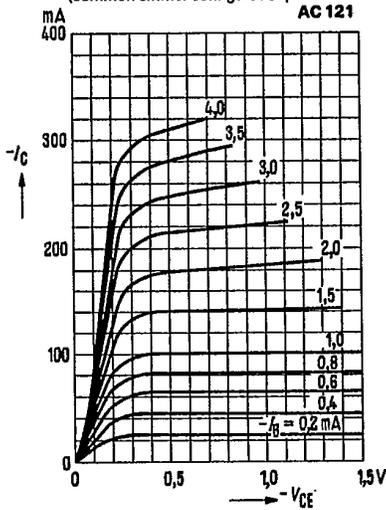
Collector current $I_C = f(V_{BE})$
 $-V_{CE} = 0.5\text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)
 AC 121, AC 152



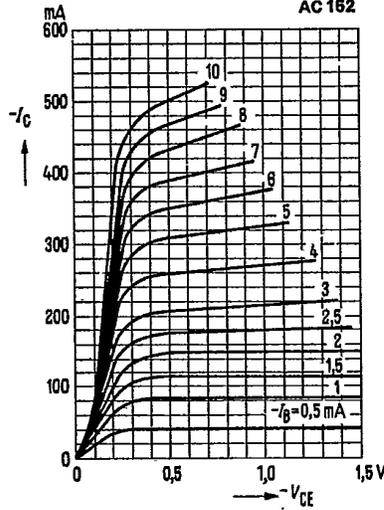
Input characteristics $I_B = f(V_{BE})$
 $-V_{CE} = 0.5\text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)
 AC 121, AC 152



Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)
 AC 121



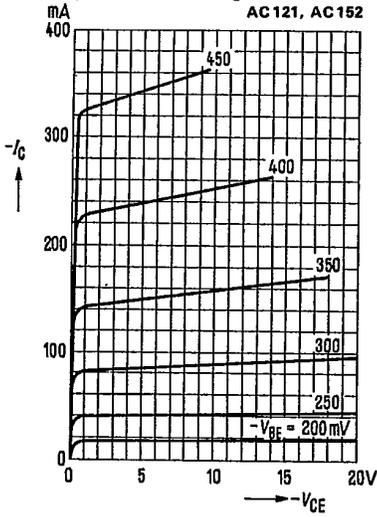
Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)
 AC 152



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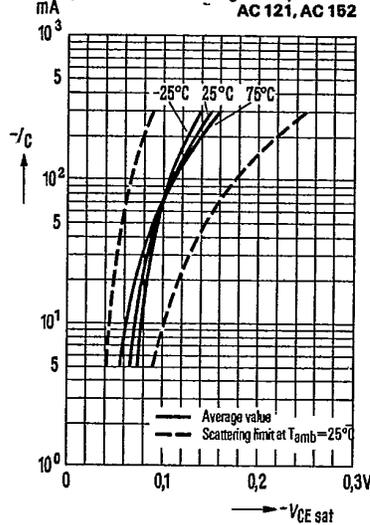
Output characteristics
 $I_C = f(V_{CE}); V_{BE} = \text{parameter}$
(common emitter configuration)

AC 121, AC 152



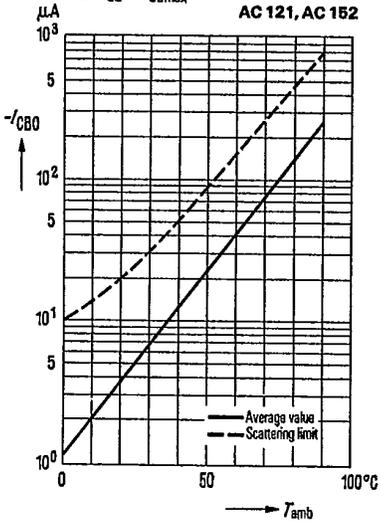
Collector emitter saturation voltage
 $V_{CEsat} = f(I_C); h_{FE} = 20$
(common emitter configuration)

AC 121, AC 152



Collector cutoff current versus temperature
 $I_{CBO} = f(T_{amb})$
For $V_{CE} = V_{CEmax}$

AC 121, AC 152



Collector-emitter voltage
 $V_{CER} = f(R_{BE})$

AC 152

